# Andre Stesmans

List of Publications by Year
in descending order

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|---|---|---|---|
| 201 papers | 6,978 citations | 61984 43 h-index | 71685 76 g-index |
| 204 all docs | 204 docs citations | 204 times ranked | 6532 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Doping-induced ferromagnetism in InSe and SnO monolayers. Journal of Computational Electronics, 2021, 20, 88-94. | 2.5 | 8 |
| 2 | Measurement of direct and indirect bandgaps in synthetic ultrathin MoS2 and WS2 films from photoconductivity spectra. Journal of Applied Physics, 2021, 129, . | 2.5 | 5 |
| 3 | Internal photoemission of electrons from 2D semiconductor/3D metal barrier structures. Journal Physics D: Applied Physics, 2021, 54, 295101. | 2.8 | 1 |
| 4 | Dangling bond defects in silicon-passivated strained-Si1â^'xGex channel layers. Journal of Materials Science: Materials in Electronics, 2020, 31, 75-79. | 2.2 | 0 |
| 5 | Two-dimensional gallium and indium oxides from global structure searching: Ferromagnetism and half metallicity via hole doping. Journal of Applied Physics, 2020, 128, 034304. | 2.5 | 12 |
| 6 | Contact resistance at 2D metal/semiconductor heterostructures. Frontiers of Nanoscience, 2020, 17, 127-140. | 0.6 | 0 |
| 7 | Band alignment at interfaces of two-dimensional materials: internal photoemission analysis. Journal of Physics Condensed Matter, 2020, 32, 413002. | 1.8 | 10 |
| 8 | Variations of paramagnetic defects and dopants in geo-MoS2 from diverse localities probed by ESR. Journal of Chemical Physics, 2020, 152, 234702. | 3.0 | 4 |
| 9 | Analysis of Transferred MoS<sub>2</sub> Layers Grown by MOCVD: Evidence of Mo Vacancy Related Defect Formation. ECS Journal of Solid State Science and Technology, 2020, 9, 093001. | 1.8 | 9 |
| 10 | First-Principles Study of the Contact Resistance at 2D Metal/2D Semiconductor Heterojunctions. Applied Sciences (Switzerland), 2020, 10, 2731. | 2.5 | 7 |
| 11 | Ferromagnetism and half-metallicity in two-dimensional <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>M</mml:mi><mml:mi mathvariant="normal">O</mml:mi><mml:mo>Â</mml:mo><mml:mo>(</mml:mo><mml:mi>M</mml:mi><mml:mo>=</mml:mo><mml monolayers induced by hole doping. Physical Review Materials, 2020, 4, . | 2.4 | 15 |
| 12 | Contact Resistance at MoS<sub>2</sub>-Based 2D Metal/Semiconductor Lateral Heterojunctions. ACS Applied Nano Materials, 2019, 2, 760-766. | 5.0 | 19 |
| 13 | Evaluation of the effective work-function of monolayer graphene on silicon dioxide by internal photoemission spectroscopy. Thin Solid Films, 2019, 674, 39-43. | 1.8 | 7 |
| 14 | Thermal stability and temperature dependent electron spin resonance characteristics of the As acceptor in geological 2H-MoS<sub>2</sub>. Semiconductor Science and Technology, 2019, 34, 035022. | 2.0 | 2 |
| 15 | Energy Band Alignment of a Monolayer MoS 2 with SiO 2 and Al 2 O 3 Insulators from Internal Photoemission. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800616. | 1.8 | 11 |
| 16 | Aryl-viologen pentapeptide self-assembled conductive nanofibers. Chemical Communications, 2019, 55, 7354-7357. | 4.1 | 12 |
| 17 | Determination of energy thresholds of electron excitations at semiconductor/insulator interfaces using trap-related displacement currents. Microelectronic Engineering, 2019, 215, 110992. | 2.4 | 3 |
| 18 | Contact resistance at graphene/MoS2 lateral heterostructures. Applied Physics Letters, 2019, 114, . | 3.3 | 14 |

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|---|---|---|---|
| 19 | Impact of MoS<sub>2</sub> layer transfer on electrostatics of MoS<sub>2</sub>/SiO<sub>2</sub> interface. Nanotechnology, 2019, 30, 055702. | 2.6 | 11 |
| 20 | On the chemistry and electrochemistry of LiPON breakdown. Journal of Materials Chemistry A, 2018, 6, 4848-4859. | 10.3 | 44 |
| 21 | Silicene on non-metallic substrates: Recent theoretical and experimental advances. Nano Research, 2018, 11, 1169-1182. | 10.4 | 31 |
| 22 | Internal Photoemission Metrology of Inhomogeneous Interface Barriers. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700865. | 1.8 | 14 |
| 23 | Band alignment at interfaces of synthetic few-monolayer MoS2 with SiO2 from internal photoemission. APL Materials, 2018, 6, . | 5.1 | 17 |
| 24 | Advances in SiCN-SiCN Bonding with High Accuracy Wafer-to-Wafer (W2W) Stacking Technology. , 2018, , . | | 24 |
| 25 | Hole-Doped 2D InSe for Spintronic Applications. ACS Applied Nano Materials, 2018, 1, 6656-6665. | 5.0 | 41 |
| 26 | Two-Dimensional Crystal Grain Size Tuning in WS<sub>2</sub> Atomic Layer Deposition: An Insight in the Nucleation Mechanism. Chemistry of Materials, 2018, 30, 7648-7663. | 6.7 | 57 |
| 27 | Ferromagnetism in two-dimensional hole-doped SnO. AIP Advances, 2018, 8, . | 1.3 | 22 |
| 28 | Nitrogen acceptor in 2H-polytype synthetic MoS2 assessed by multifrequency electron spin resonance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, . | 2.1 | 5 |
| 29 | Structural Properties of Alâ€“O Monolayers in SiO<sub>2</sub> on Silicon and the Maximization of Their Negative Fixed Charge Density. ACS Applied Materials & Interfaces, 2018, 10, 30495-30505. | 8.0 | 30 |
| 30 | Paramagnetic Intrinsic Defects in Polycrystalline Large-Area 2D MoS2 Films Grown on SiO2 by Mo Sulfurization. Nanoscale Research Letters, 2017, 12, 283. | 5.7 | 12 |
| 31 | (Invited) Internal Photoemission of Electrons from 2-Dimensional Semiconductors. ECS Transactions, 2017, 80, 191-201. | 0.5 | 12 |
| 32 | ESR identification of the nitrogen acceptor in 2H-polytype synthetic MoS2: Dopant level and activation. AIP Advances, 2017, 7, 105006. | 1.3 | 10 |
| 33 | Leakage current induced by surfactant residues in self-assembly based ultralow-k dielectric materials. Applied Physics Letters, 2017, 111, . | 3.3 | 8 |
| 34 | The lead acceptor in p-type natural 2H-polytype MoS<sub>2</sub> crystals evidenced by electron paramagnetic resonance. Journal of Physics Condensed Matter, 2017, 29, 08LT01. | 1.8 | 10 |
| 35 | The Nitrogen Acceptor in 2Hâ€Polytype Synthetic MoS <sub>2</sub> : Frequency and Temperature Dependent ESR Analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700211. | 0.8 | 4 |
| 36 | Controlled Sulfurization Process for the Synthesis of Large Area MoS<sub>2</sub> Films and MoS<sub>2</sub>/WS<sub>2</sub> Heterostructures. Advanced Materials Interfaces, 2016, 3, 1500635. | 3.7 | 61 |

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| 37 | Electron energy distribution in Si/TiN and Si/Ru hybrid floating gates with hafnium oxide based insulators for charge trapping memory devices. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 265-269. | 1.8 | 1 |
| 38 | Photonic nanostructures for advanced light trapping in silicon solar cells: the impact of etching on the material electronic quality. Physica Status Solidi - Rapid Research Letters, 2016, 10, 158-163. | 2.4 | 10 |
| 39 | ESR study of p-type natural 2H-polytype MoS2 crystals: The As acceptor activity. Applied Physics Letters, 2016, 109, . | 3.3 | 14 |
| 40 | Band offsets and trap-related electron transitions at interfaces of (100)InAs with atomic-layer deposited Al2O3. Journal of Applied Physics, 2016, 120, 235701. | 2.5 | 5 |
| 41 | Silicene nanoribbons on transition metal dichalcogenide substrates: Effects on electronic structure and ballistic transport. Nano Research, 2016, 9, 3394-3406. | 10.4 | 8 |
| 42 | Effect of La doping on interface barrier between Si-passivated Ge and insulating HfO2. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 855-859. | 0.8 | 0 |
| 43 | Oxygen and hydroxyl adsorption on MS<sub>2</sub> (M = Mo, W, Hf) monolayers: a firstâ€principles molecular dynamics study. Physica Status Solidi - Rapid Research Letters, 2016, 10, 787-791. | 2.4 | 7 |
| 44 | Hydrogen induced dipole at the Pt/oxide interface in MOS devices. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 260-264. | 1.8 | 5 |
| 45 | Impact of point defects on the electronic and transport properties of silicene nanoribbons. Journal of Physics Condensed Matter, 2016, 28, 035302. | 1.8 | 25 |
| 46 | Topological to trivial insulating phase transition in stanene. Nano Research, 2016, 9, 774-778. | 10.4 | 32 |
| 47 | Electrical Characterization of Ultrathin RF-Sputtered LiPON Layers for Nanoscale Batteries. ACS Applied Materials & Interfaces, 2016, 8, 7060-7069. | 8.0 | 63 |
| 48 | Functional silicene and stanene nanoribbons compared to graphene: electronic structure and transport. 2D Materials, 2016, 3, 015001. | 4.4 | 18 |
| 49 | First-principles investigation of defects at GaAs/oxide interfaces. Materials Science in Semiconductor Processing, 2016, 42, 239-241. | 4.0 | 1 |
| 50 | Band alignment at interfaces of few-monolayer MoS2 with SiO2 and HfO2. Microelectronic Engineering, 2015, 147, 294-297. | 2.4 | 31 |
| 51 | High Cycling Stability and Extreme Rate Performance in Nanoscaled LiMn<sub>2</sub>O<sub>4</sub> Thin Films. ACS Applied Materials & Interfaces, 2015, 7, 22413-22420. | 8.0 | 59 |
| 52 | Band alignment and effective work function of atomic-layer deposited VO2 and V2 O5 films on SiO2 and Al2 O3. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 238-241. | 0.8 | 5 |
| 53 | Inherent interface defects in thermal (211)Si/SiO2:29Si hyperfine interaction. , 2014, , . | | 0 |
| 54 | Band alignment at interfaces of amorphous Al2O3 with Ge1â^'xSnx- and strained Ge-based channels. Applied Physics Letters, 2014, 104, 202107. | 3.3 | 4 |

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|---|---|---|---|
| 55 | Current-voltage characteristics of armchair Sn nanoribbons. Physica Status Solidi - Rapid Research Letters, 2014, 8, 931-934. | 2.4 | 12 |
| 56 | Magnetic defects in chemically converted graphene nanoribbons: electron spin resonance investigation. AIP Advances, 2014, 4, . | 1.3 | 10 |
| 57 | Reducing exciton-polaron annihilation in organic planar heterojunction solar cells. Physical Review B, 2014, 90, . | 3.2 | 14 |
| 58 | First-principles study of strained 2D MoS2. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 56, 416-421. | 2.7 | 119 |
| 59 | Decreased Recombination Through the Use of a Nonâ€Fullerene Acceptor in a 6.4% Efficient Organic Planar Heterojunction Solar Cell. Advanced Energy Materials, 2014, 4, 1301413. | 19.5 | 75 |
| 60 | Large Area Carbon Nanosheet Capacitors. ECS Solid State Letters, 2014, 3, N8-N10. | 1.4 | 5 |
| 61 | Effect of Binder Content in Cuâ€“Inâ€“Se Precursor Ink on the Physical and Electrical Properties of Printed CuInSe<sub>2</sub> Solar Cells. Journal of Physical Chemistry C, 2014, 118, 27201-27209. | 3.1 | 9 |
| 62 | Modulation of electron barriers between Ti<scp>N</scp><sub>x</sub> and oxide insulators (<scp>S</scp>i<scp>O</scp><sub>2</sub>, Al<sub>2</sub><scp>O</scp><sub>3</sub>) using Ti interlayer. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 382-388. | 1.8 | 4 |
| 63 | Influence of the bulkiness of the substituent on the aggregation and magnetic properties of poly(3â€alkylthiophene)s. Journal of Polymer Science Part A, 2014, 52, 76-86. | 2.3 | 11 |
| 64 | Multi-frequency electron spin resonance study of inherent Si dangling bond defects at the thermal (211)Si/SiO2interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1589-1592. | 0.8 | 2 |
| 65 | Generation of Si dangling bond defects at Si/insulator interfaces induced by oxygen scavenging. Physica Status Solidi (B): Basic Research, 2014, 251, 2193-2196. | 1.5 | 4 |
| 66 | Charge transition level of GeP<sub>b1</sub> centers at interfaces of SiO<sub>2</sub>/Ge<sub>x</sub>Si<sub>1â^'x</sub>/SiO<sub>2</sub> heterostructures investigated by positron annihilation spectroscopy. Physica Status Solidi (B): Basic Research, 2014, 251, 2211-2215. | 1.5 | 1 |
| 67 | The origin of white luminescence from silicon oxycarbide thin films. Applied Physics Letters, 2014, 104, . | 3.3 | 45 |
| 68 | (Invited) Nature of Point Defects at High-Mobility Semiconductor/Interfaces Probed by Electron Spin Resonance: Thermal GaAs/GaAs-Oxide Structures. ECS Transactions, 2014, 64, 293-299. | 0.5 | 0 |
| 69 | Vibrational properties of epitaxial silicene layers on (111) Ag. Applied Surface Science, 2014, 291, 113-117. | 6.1 | 49 |
| 70 | Impact of strain on the passivation efficiency of Ge dangling bond interface defects in condensation grown SiO2/GexSi1â^'x/SiO2/(100)Si structures with nm-thin GexSi1â^'x layers. Applied Surface Science, 2014, 291, 11-15. | 6.1 | 4 |
| 71 | Processing-induced near-interfacial thermal donor generation in (100)Si/Si-oxycarbide insulator structures revealed by electron spin resonance. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1574-1577. | 0.8 | 0 |
| 72 | Vibrational properties of silicene and germanene. Nano Research, 2013, 6, 19-28. | 10.4 | 144 |

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| 73 | High-resolution electron spin resonance analysis of ion bombardment induced defects in advanced low-Î¹ insulators (Î¹â€‰=â€‰2.0-2.5). Applied Physics Letters, 2013, 102, . | 3.3 | 15 |
| 74 | Improved cathode buffer layer to decrease exciton recombination in organic planar heterojunction solar cells. Applied Physics Letters, 2013, 102, . | 3.3 | 21 |
| 75 | Chemical kinetics of the hydrogen-GePb1 defect interaction at the (100)GexSi1â^'x/SiO2 interface. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 010603. | 1.2 | 3 |
| 76 | Electron band alignment at the interface of (100)InSb with atomic-layer deposited Al<sub>2</sub>O<sub>3</sub>. Applied Physics Letters, 2012, 101, 082114. | 3.3 | 11 |
| 77 | Oxidation of the GaAs(001) surface: Insights from first-principles calculations. Physical Review B, 2012, 85, . | 3.2 | 18 |
| 78 | Near-interface Si substrate 3d metal contamination during atomic layer deposition processing detected by electron spin resonance. Journal of Applied Physics, 2012, 111, . | 2.5 | 8 |
| 79 | Interface nature of oxidized single-crystal arrays of etched Si nanowires on (100)Si. Applied Physics Letters, 2012, 100, 082110. | 3.3 | 6 |
| 80 | Correlation between interface traps and paramagnetic defects in c-Si/a-Si:H heterojunctions. Applied Physics Letters, 2012, 100, . | 3.3 | 15 |
| 81 | Interface barriers at the interfaces of polar GaAs(111) faces with Al2O3. Applied Physics Letters, 2012, 100, . | 3.3 | 9 |
| 82 | Semiconducting-like filament formation in TiN/HfO2/TiN resistive switching random access memories. Applied Physics Letters, 2012, 100, . | 3.3 | 43 |
| 83 | Electrically active defects at AlN/Si interface studied by DLTS and ESR. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1851-1856. | 1.8 | 17 |
| 84 | Strain-induced semiconductor to metal transition in the two-dimensional honeycomb structure of MoS2. Nano Research, 2012, 5, 43-48. | 10.4 | 620 |
| 85 | Transitivity of band offsets between semiconductor heterojunctions and oxide insulators. Applied Physics Letters, 2011, 99, . | 3.3 | 20 |
| 86 | Inelastic electron tunneling spectroscopy of HfO2 gate stacks: A study based on first-principles modeling. Applied Physics Letters, 2011, 99, 132101. | 3.3 | 0 |
| 87 | Electronic properties of hydrogenated silicene and germanene. Applied Physics Letters, 2011, 98, . | 3.3 | 399 |
| 88 | Universal stress-defect correlation at (100)semiconductor/oxide interfaces. Applied Physics Letters, 2011, 98, 141901. | 3.3 | 10 |
| 89 | TiN x / HfO 2 interface dipole induced by oxygen scavenging. Applied Physics Letters, 2011, 98, . | 3.3 | 34 |
| 90 | Band Alignment at Interfaces of Oxide Insulators with Semiconductors. Integrated Ferroelectrics, 2011, 125, 53-60. | 0.7 | 5 |

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| 91 | Interface state energy distribution and Pb defects at Si(110)/SiO2 interfaces: Comparison to (111) and (100) silicon orientations. Journal of Applied Physics, 2011, 109, . | 2.5 | 61 |
| 92 | First-principles study of Ge dangling bonds in GeO2 and correlation with electron spin resonance at Ge/GeO2 interfaces. Applied Physics Letters, 2011, 99, . | 3.3 | 11 |
| 93 | Influence of Al<sub>2</sub>O<sub>3</sub> crystallization on band offsets at interfaces with Si and TiN<sub>x</sub>. Applied Physics Letters, 2011, 99, 072103. | 3.3 | 50 |
| 94 | Electron band alignment at the interface of (100)GaSb with molecular-beam deposited Al2O3. Applied Physics Letters, 2011, 98, 072102. | 3.3 | 7 |
| 95 | Structural and vibrational properties of amorphous GeO2 from first-principles. Applied Physics Letters, 2011, 98, . | 3.3 | 6 |
| 96 | Electronic structure of NiO layers grown on Al2O3 and SiO2 using metallo-organic chemical vapour deposition. Journal of Applied Physics, 2011, 110, . | 2.5 | 4 |
| 97 | Defects in Low-k Insulators (Î²=2.5 â€“ 2.0): ESR Analysis and Charge Injection. Materials Research Society Symposia Proceedings, 2011, 1335, 119. | 0.1 | 3 |
| 98 | Electron energy band alignment at the NiO/SiO2 interface. Applied Physics Letters, 2010, 96, . | 3.3 | 7 |
| 99 | Comparative electron spin resonance study of epi-Lu2O3/(111)Si and a-Lu2O3/(100)Si interfaces: Misfit point defects. Journal of Applied Physics, 2010, 107, 094502. | 2.5 | 4 |
| 100 | Electron energy band alignment at the (100)Si/MgO interface. Applied Physics Letters, 2010, 96, . | 3.3 | 11 |
| 101 | Pb(0) centers at the Si-nanocrystal/SiO2 interface as the dominant photoluminescence quenching defect. Journal of Applied Physics, 2010, 107, 084309. | 2.5 | 41 |
| 102 | Influence of in situ applied ultrasound during Si+ implantation in SiO2 on paramagnetic defect generation. Journal of Applied Physics, 2010, 107, . | 2.5 | 11 |
| 103 | Low temperature silicon dioxide by thermal atomic layer deposition: Investigation of material properties. Journal of Applied Physics, 2010, 107, . | 2.5 | 86 |
| 104 | Can silicon behave like graphene? A first-principles study. Applied Physics Letters, 2010, 97, . | 3.3 | 208 |
| 105 | Magnetic Properties of Substituted Poly(thiophene)s in Their Neutral State. Macromolecules, 2010, 43, 2910-2915. | 4.8 | 13 |
| 106 | Electron band alignment between (100)InP and atomic-layer deposited Al2O3. Applied Physics Letters, 2010, 97, 132112. | 3.3 | 17 |
| 107 | Nitrogen at the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Si-nanocrystal</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext> and its influence on luminescence and interface defects. Physical Review B, 2010, 82, . | 3.2 | 44 |
| 108 | Electronic properties of two-dimensional hexagonal germanium. Applied Physics Letters, 2010, 96, . | 3.3 | 114 |

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| 109 | A theoretical study of the initial oxidation of the GaAs(001)-Î²2(2Ã—4) surface. Applied Physics Letters, 2009, 95, . | 3.3 | 31 |
| 110 | Nontrigonal Ge dangling bond interface defect in condensation-grown<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>100</mml:mn></mml:mrow><mml:mo>)</m Physical Review B, 2009, 79, . | 3.2 | 28 |
| 111 | Valence band energy in confined Si1âˆ’xGex (0.28<x<0.93) layers. Applied Physics Letters, 2009, 94, 172106. | 3.3 | 18 |
| 112 | Electronic properties of Ge dangling bond centers at Si1âˆ’xGex/SiO2 interfaces. Applied Physics Letters, 2009, 95, 222106. | 3.3 | 17 |
| 113 | First-principles study of the electronic properties of Ge dangling bonds at (100)Si1âˆ’xGex/SiO2 interfaces. Applied Physics Letters, 2009, 95, . | 3.3 | 10 |
| 114 | Energy barriers at interfaces between (100) InxGa1âˆ’xAsâ€ˆ(â‰xâ‰0.53) and atomic-layer deposited Al2O3 and HfO2. Applied Physics Letters, 2009, 94, . | 3.3 | 24 |
| 115 | Electron spin resonance observation of an interfacial GeP<sub>b1</sub>-type defect in SiO<sub>2</sub>(100)Si<sub>1âˆ’x</sub>Ge<sub>x</sub>SiO<sub>2</sub>Si heterostructures. Journal of Physics Condensed Matter, 2009, 21, 122201. | 1.8 | 10 |
| 116 | Alternative techniques to reduce interface traps in nâ€type 4Hâ€SiC MOS capacitors. Physica Status Solidi (B): Basic Research, 2008, 245, 1378-1389. | 1.5 | 64 |
| 117 | Electronic structure of the interface of aluminum nitride with Si(100). Journal of Applied Physics, 2008, 104, 093713. | 2.5 | 25 |
| 118 | Paramagnetic point defects at interfacial layers in biaxial tensile strained (100)Si/SiO2. Journal of Applied Physics, 2008, 103, . | 2.5 | 17 |
| 119 | Paramagnetic point defects at SiO2/nanocrystalline Si interfaces. Applied Physics Letters, 2008, 93, . | 3.3 | 22 |
| 120 | Photoconductivity of Hf-based binary metal oxide systems. Journal of Applied Physics, 2008, 104, 114103. | 2.5 | 12 |
| 121 | Misfit point defects at the epitaxial Lu2O3/(111)Si interface revealed by electron spin resonance. Applied Physics Letters, 2008, 93, 103505. | 3.3 | 4 |
| 122 | Beneficial effect of La on band offsets in Ge/high-Îº insulator structures with GeO2 and La2O3 interlayers. Applied Physics Letters, 2008, 93, 102115. | 3.3 | 16 |
| 123 | The effect of implanting boron on the optical absorption and electron paramagnetic resonance spectra of silica. Journal of Applied Physics, 2008, 104, 054110. | 2.5 | 2 |
| 124 | Influence of metal capping layer on the work function of Mo gated metal-oxide semiconductor stacks. Applied Physics Letters, 2008, 93, 083511. | 3.3 | 3 |
| 125 | Energy barriers at interfaces of (100)GaAs with atomic layer deposited Al2O3 and HfO2. Applied Physics Letters, 2008, 93, . | 3.3 | 30 |
| 126 | Internal photoemission of electrons from Ta-based conductors into SiO2 and HfO2 insulators. Journal of Applied Physics, 2008, 104, . | 2.5 | 7 |

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|---|---|---|---|
| 127 | Internal photoemission at interfaces of high-Î¹ insulators with semiconductors and metals. Journal of Applied Physics, 2007, 102, . | 2.5 | 223 |
| 128 | Analysis of the (100)Si/LaAlO3 structure by electron spin resonance: nature of the interface. Journal of Materials Science: Materials in Electronics, 2007, 18, 735-741. | 2.2 | 0 |
| 129 | Ruthenium gate electrodes on SiO2 and HfO2: Sensitivity to hydrogen and oxygen ambients. Applied Physics Letters, 2006, 88, 243514. | 3.3 | 44 |
| 130 | Probing Semiconductor/Insulator Heterostructures Through Electron Spin Resonance of Point Defects: Interfaces, Interlayers, and Stress. Materials Research Society Symposia Proceedings, 2006, 984, 1. | 0.1 | 0 |
| 131 | High open-circuit voltage values on fine-grained thin-film polysilicon solar cells. Journal of Applied Physics, 2006, 100, 063702. | 2.5 | 41 |
| 132 | Effective work function modulation by controlled dielectric monolayer deposition. Applied Physics Letters, 2006, 89, 113505. | 3.3 | 29 |
| 133 | Reaction-dispersive proton transport model for negative bias temperature instabilities. Applied Physics Letters, 2005, 86, 093506. | 3.3 | 51 |
| 134 | Interface traps and dangling-bond defects in (100)Geâ•HfO2. Applied Physics Letters, 2005, 87, 032107. | 3.3 | 119 |
| 135 | Defect generation in high Î¹ gate dielectric stacks under electrical stress: the impact of hydrogen. Journal of Physics Condensed Matter, 2005, 17, S2075-S2088. | 1.8 | 33 |
| 136 | Conduction band-edge States associated with the removal of d-state degeneracies by the Jahn-Teller effect. IEEE Transactions on Device and Materials Reliability, 2005, 5, 65-83. | 2.0 | 63 |
| 137 | Energy band alignment at the (100)Ge/HfO2 interface. Applied Physics Letters, 2004, 84, 2319-2321. | 3.3 | 107 |
| 138 | Stable trapping of electrons and holes in deposited insulating oxides: Al2O3, ZrO2, and HfO2. Journal of Applied Physics, 2004, 95, 2518-2526. | 2.5 | 74 |
| 139 | Vacancy clusters in diamond studied by electron spin resonance. Physica Status Solidi A, 2004, 201, 2509-2515. | 1.7 | 10 |
| 140 | Energy distribution of the (100)Si/HfO2 interface states. Applied Physics Letters, 2004, 84, 4771-4773. | 3.3 | 30 |
| 141 | Si dangling-bond-type defects at the interface of (100)Si with ultrathin HfO2. Applied Physics Letters, 2003, 82, 4074-4076. | 3.3 | 91 |
| 142 | Invasive nature of corona charging on thermal Si/SiO2 structures with nanometer-thick oxides revealed by electron spin resonance. Applied Physics Letters, 2003, 82, 2835-2837. | 3.3 | 23 |
| 143 | Pb-type interface defects in (100)Si/SiO2 structures grown in ozonated water solution. Journal of Applied Physics, 2003, 93, 4331-4333. | 2.5 | 2 |
| 144 | Annealing Induced Degradation of Thermal SiO2On (100)Si: Point Defect Generation. Radiation Effects and Defects in Solids, 2003, 158, 419-425. | 1.2 | 1 |

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|---|---|---|---|
| 145 | Si dangling-bond-type defects at the interface of (100)Si with ultrathin layers of SiOx, Al2O3, and ZrO2. Applied Physics Letters, 2002, 80, 1957-1959. | 3.3 | 92 |
| 146 | Influence of interface relaxation on passivation kinetics in H2 of coordination Pb defects at the (111)Si/SiO2 interface revealed by electron spin resonance. Journal of Applied Physics, 2002, 92, 1317-1328. | 2.5 | 63 |
| 147 | Characterization of S centers generated by thermal degradation in SiO2 on (100)Si. Applied Physics Letters, 2002, 80, 4753-4755. | 3.3 | 4 |
| 148 | Hole trapping in ultrathin Al2O3 and ZrO2 insulators on silicon. Applied Physics Letters, 2002, 80, 1261-1263. | 3.3 | 35 |
| 149 | Defects at the interface of (100)Si with ultrathin layers of SiO[sub x], Al[sub 2]O[sub 3], and ZrO[sub 2] probed by electron spin resonance. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1720. | 1.6 | 11 |
| 150 | ESR and Photo-ESR Study of Defects in CVD Diamond. Physica Status Solidi A, 2002, 193, 448-456. | 1.7 | 13 |
| 151 | Synthesis and characterization of sol-gel derived ZnS : Mn2+ nanocrystallites embedded in a silica matrix. Bulletin of Materials Science, 2002, 25, 175-180. | 1.7 | 105 |
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